TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOS V)

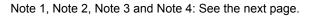
# **TPC8117**

### Lithium Ion Battery Applications Notebook PC Applications

- Small footprint due to small and thin package
- Low drain-source ON-resistance  $: R_{DS}(ON) = 3.0 \text{ m}\Omega \text{ (typ.)}$
- High forward transfer admittance  $|Y_{fs}| = 54 \text{ S (typ.)}$
- Low leakage current:  $I_{DSS} = -10 \ \mu A \ (max) \ (V_{DS} = -30 \ V)$
- Enhancement mode:  $V_{th} = -0.8$  to -2.0 V ( $V_{DS} = -10$  V,  $I_D = -1$  mA)

#### Absolute Maximum Ratings (Ta = 25°C)

| Characteri                | stics  | Symbol           | Rating     | Unit |  |
|---------------------------|--|------------------|------------|------|--|
| Drain-source voltage      |  | V <sub>DSS</sub> | -30        | V    |  |
| Drain-gate voltage (R     | <sub>GS</sub> = 20 kΩ)                         | V <sub>DGR</sub> | -30        | V    |  |
| Gate-source voltage       |  | V <sub>GSS</sub> | ±20        | V    |  |
| Drain current             | DC (Note 1)                                    | ۱ <sub>D</sub>   | -18        | ^    |  |
| Drain current             | Pulse (Note 1)                                 | I <sub>DP</sub>  | -72        | A    |  |
| Drain power dissipatio    | n (t = 10 s)<br>(Note 2a)                      | PD               | 1.9        | W    |  |
| Drain power dissipatio    | n (t = 10 s)<br>(Note 2b)                      | PD               | 1.0        | W    |  |
| Single pulse avalanch     | e energy<br>(Note 3)                           | E <sub>AS</sub>  | 211        | mJ   |  |
| Avalanche current         |  | I <sub>AR</sub>  | -18        | А    |  |
|                           | etitive avalanche energy<br>(Note 2a) (Note 4) |                  | 0.030      | mJ   |  |
| Channel temperature       |  | T <sub>ch</sub>  | 150        | °C   |  |
| Storage temperature range |  | T <sub>stg</sub> | -55 to 150 | °C   |  |



Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating

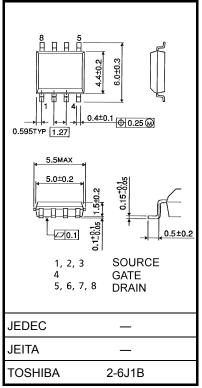
temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating

Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

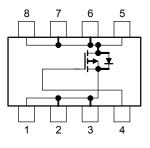
This transistor is an electrostatic-sensitive device. Handle with care.





Weight: 0.080 g (typ.)

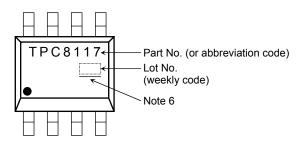
### **Circuit Configuration**



## Thermal Characteristics

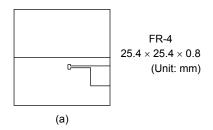
| Characteristics  | Symbol                 | Max  | Unit |
|--|------------------------|------|------|
| Thermal resistance, channel to ambient<br>(t = 10 s) (Note 2a) | R <sub>th (ch-a)</sub> | 65.8 | °C/W |
| Thermal resistance, channel to ambient<br>(t = 10 s) (Note 2b) | R <sub>th (ch-a)</sub> | 125  | °C/W |

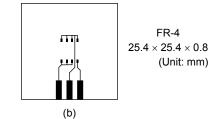
# Marking (Note 5)



Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)





Note 3:  $V_{DD} = -24$  V,  $T_{ch} = 25^{\circ}C$  (initial),  $L = 500 \ \mu$ H,  $R_G = 25 \ \Omega$ ,  $I_{AR} = -18$  A

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: • on the lower left of the marking indicates Pin 1.

\* Weekly code: (Three digits)



Note 6: A line under a Lot No. identifies the indication of product Labels. Not underlined: [[Pb]]/INCLUDES > MCV Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

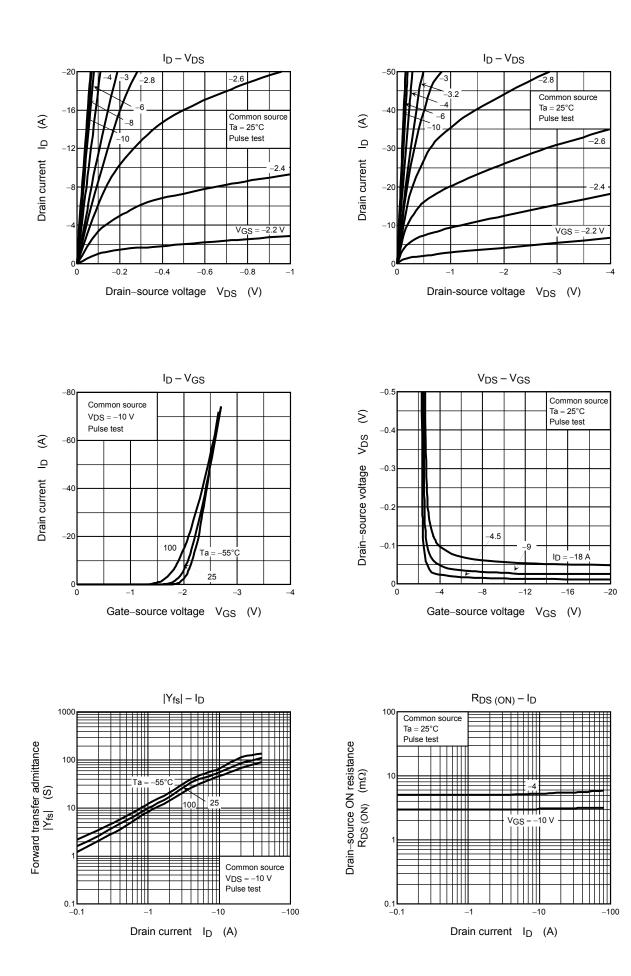
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

Electrical Characteristics (Ta = 25°C)

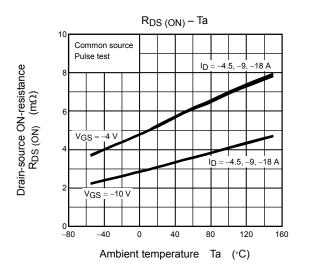
| Cha   | racteristics                                | Symbol               | Test Condition  | Min                      | Тур.  | Max  | Unit |
|---|---|----------------------|---|--------------------------|---|------|------|
| Gate leakage curre                              | ent   | I <sub>GSS</sub>     | $V_{GS}=\pm 20~V,~V_{DS}=0~V$   | _                        | —   | ±100 | nA   |
| Drain cut-OFF cur                               | rent  | I <sub>DSS</sub>     | $V_{DS} = -30$ V, $V_{GS} = 0$ V  |                          | _   | -10  | μA   |
| Drain-source brea                               | kdown voltago                               | V (BR) DSS           | $I_{D} = -10$ mA, $V_{GS} = 0$ V  | -30                      | _   |      | v    |
| Drain-source brea                               | Kuowii vollage                              | V (BR) DSX           | $I_D = -10$ mA, $V_{GS} = 20$ V   | -13                      | _   |      | v    |
| Gate threshold vol                              | tage  | V <sub>th</sub>      | $V_{DS} = -10 \text{ V}, \text{ I}_{D} = -1 \text{ mA}$                           | -0.8 — -2.0<br>— 5.5 7.9 |   | V    |      |
|   |   |                      | $V_{GS} = -4 \text{ V}, \text{ I}_D = -9 \text{ A}$                               | _                        | 5.5   | 7.9  | mΩ   |
| Drain-source ON-resistance                      |   | R <sub>DS (ON)</sub> | $V_{GS} = -10 \text{ V}, \text{ I}_{D} = -9 \text{ A}$                            | _                        | 3.0   | 3.9  |      |
| Forward transfer admittance                     |   | Y <sub>fs</sub>      | $V_{DS} = -10 \text{ V}, \text{ I}_{D} = -9 \text{ A}$                            | 27                       | 54  | _    | S    |
| Input capacitance                               | ut capacitance                              |                      | $V_{DS} = -10 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$ | _                        | 4600  | _    | pF   |
| Reverse transfer capacitance                    |   | C <sub>rss</sub>     |   | _                        | 970   | _    |      |
| Reverse transfer capacitance Output capacitance |   | C <sub>oss</sub>     |   | _                        | 1500  |      |      |
|   | Rise time                                   | tr                   | $V_{CS} = 0 V \int I_D = -9 A$  |                          | 10  | _    | - ns |
| Switching time                                  | Turn-ON time                                | t <sub>on</sub>      | $V_{GS} \xrightarrow{0}_{-10} V \xrightarrow{I_D = -9} A$                         | _                        | $\begin{array}{c ccccccccccccccccccccccccccccccccccc$ | _    |      |
| Switching time                                  | Fall time                                   | t <sub>f</sub>       | RL=1  | _                        | 300   | _    |      |
|   | Turn-OFF time                               | t <sub>off</sub>     | $V_{DD}\approx -15~V \label{eq:DD}$ Duty $\leq$ 1%, $t_W=$ 10 $\mu s$             | _                        | 800   |      |      |
| Total gate charge (gate-source plus             | al gate charge<br>e-source plus gate-drain) |                      | V <sub>DD</sub> ≈ -24 V, V <sub>GS</sub> = -10 V,                                 |                          | 130   | _    | nC   |
| Gate-source charge 1                            |   | Q <sub>gs1</sub>     | $I_{\rm D} = -18  {\rm A}$  | _                        | 12  |      |      |
| Gate-drain ("miller") charge                    |   | Q <sub>gd</sub>      |   | _                        | 40  |      |      |

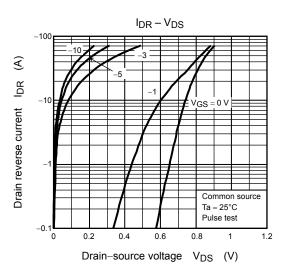
## Source-Drain Ratings and Characteristics (Ta = 25°C)

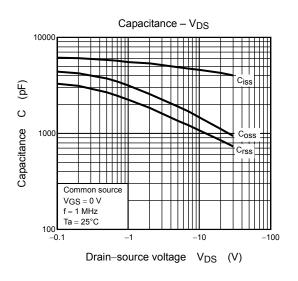
| Charac                | teristics |          | Symbol           | Test Condition   | Min | Тур. | Max | Unit |
|-----------------------|-----------|----------|------------------|--|-----|------|-----|------|
| Drain reverse current | Pulse     | (Note 1) | I <sub>DRP</sub> | —  | _   | _    | -72 | А    |
| Forward voltage (dio  | de)       |          | V <sub>DSF</sub> | $I_{DR} = -18 \text{ A}, \text{ V}_{GS} = 0 \text{ V}$ | _   |      | 1.2 | V    |

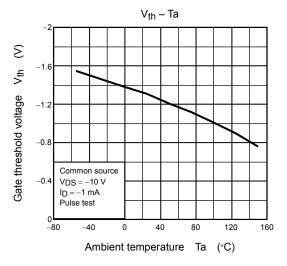


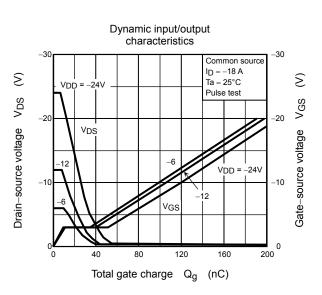
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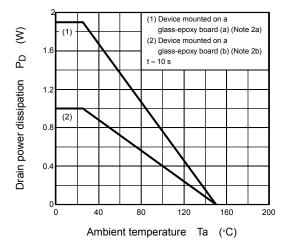


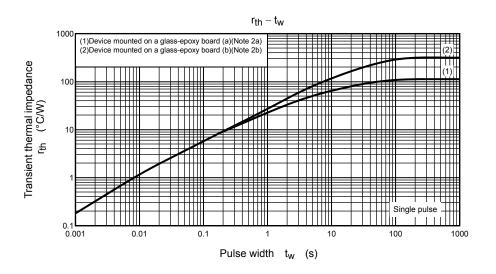


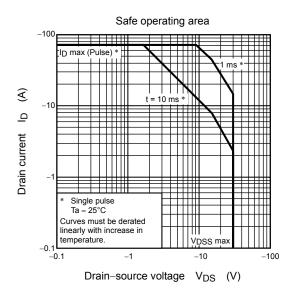












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